

Application Serial No. 16.. 29,694  
Reply to Office Action of January 21, 2005

PATENT  
Docket: CU-3477

**Amendments To The Specification**

Please replace the paragraph in the Specification page 10, lines 9-13 with the following amended paragraph:

Accordingly, the recessed portion of the storage node electrode has a broader width than that of any other portion of the storage node electrode. In this drawing, the drawing numeral 251 refers to the same a second contact hole 250 251 but formed after the completion of the wet-cleaning process. Therefore, FIG. 3E shows the second contact hole 251 having the recessed portion 180a at the bottom, but FIG. 3D does not.

Please replace the paragraph in the Specification page 12, lines 3-7 with the following amended paragraph:

As shown in Fig. 4, before forming the second interlayer insulating film 180 above the resultant substrate inclusive of the polysilicon layer 160, a silicon nitride film 320 is formed to at thickness of 300 ~ 1000 Å thereby using it as an etch barrier film in the wet-etching process.